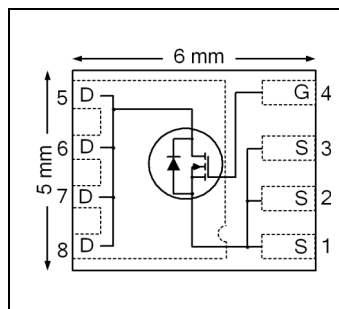


V_{DSS}	30	V
R_{DS(on)} max (@ V _{GS} = 10V)	1.3	mΩ
Q_g (typical)	50	nC
R_g (typical)	1.3	Ω
I_D (@T _{C (Bottom)} = 25°C)	275	A



Applications

- OR-ing MOSFET for 12V (typical) Bus in-Rush Current
- Battery Operated DC Motor Inverters

Features

Low R _{DS(on)} (<1.3mΩ)
Low Thermal Resistance to PCB (<0.8°C/W)
Low Profile (<0.9 mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial Qualification

results in



Benefits

Lower Conduction Losses
Enable better thermal dissipation
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFH8307PbF	PQFN 5mm x 6 mm	Tape and Reel	4000	IRFH8307TRPbF

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{GS}	Gate-to-Source Voltage	± 20	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	42	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	33	
I _D @ T _{C (Bottom)} = 25°C	Continuous Drain Current, V _{GS} @ 10V ⑥	275	
I _D @ T _{C (Bottom)} = 100°C	Continuous Drain Current, V _{GS} @ 10V ⑥	174	
I _{DM}	Pulsed Drain Current ①	1100	
P _D @ T _A = 25°C	Power Dissipation ⑤	3.6	W
P _D @ T _{C (Bottom)} = 25°C	Power Dissipation ⑤	156	
	Linear Derating Factor ⑤	0.029	W/°C
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		

Notes ① through ⑥ are on page 9

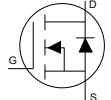
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	1.1	1.3	mΩ	V _{GS} = 10V, I _D = 50A ③
		—	1.7	2.1		V _{GS} = 4.5V, I _D = 50A ③
V _{GS(th)}	Gate Threshold Voltage	1.35	1.80	2.35	V	V _{DS} = V _{GS} , I _D = 150μA
ΔV _{GS(th)}	Gate Threshold Voltage Coefficient	—	-6.2	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	5.0	μA	V _{DS} = 24V, V _{GS} = 0V
		—	—	150		V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
g _{fs}	Forward Transconductance	190	—	—	S	V _{DS} = 15V, I _D = 50A
Q _g	Total Gate Charge	—	120	—	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 50A
Q _g	Total Gate Charge	—	50	75	nC	V _{DS} = 15V V _{GS} = 4.5V I _D = 50A See Fig. 18
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	12	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	6.5	—		
Q _{gd}	Gate-to-Drain Charge	—	16	—		
Q _{godr}	Gate Charge Overdrive	—	16	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	23	—	nC	V _{DS} = 16V, V _{GS} = 0V
Q _{oss}	Output Charge	—	30	—		
R _G	Gate Resistance	—	1.3	2.6	Ω	
t _{d(on)}	Turn-On Delay Time	—	26	—	ns	V _{DD} = 15V, V _{GS} = 4.5V I _D = 50A R _G = 1.8Ω See Fig. 17
t _r	Rise Time	—	30	—		
t _{d(off)}	Turn-Off Delay Time	—	31	—		
t _f	Fall Time	—	13	—		
C _{iss}	Input Capacitance	—	7200	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1360	—		V _{DS} = 15V
C _{rss}	Reverse Transfer Capacitance	—	590	—		f = 1.0MHz

Avalanche Characteristics

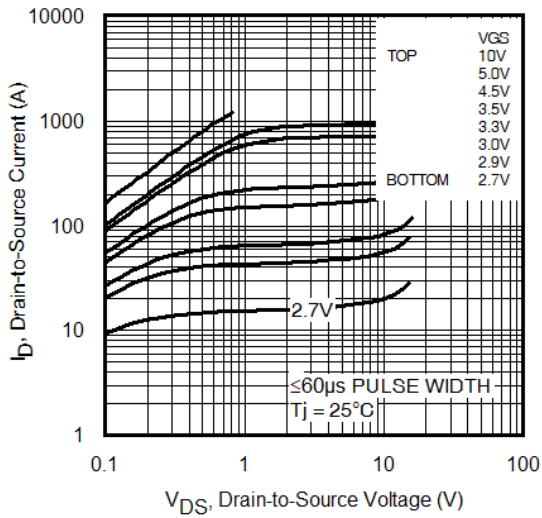
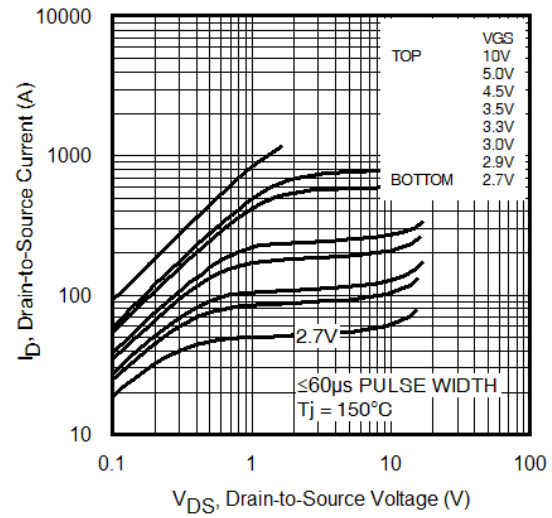
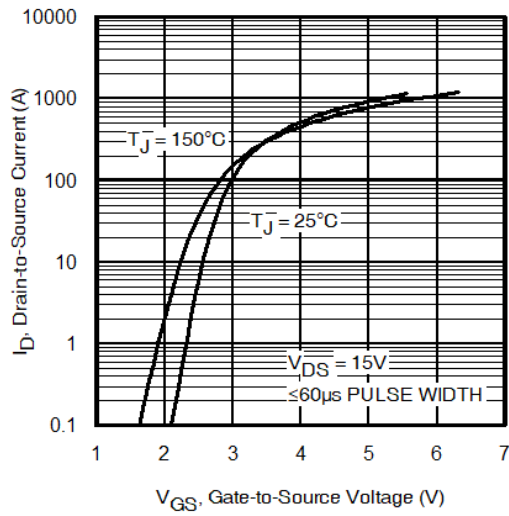
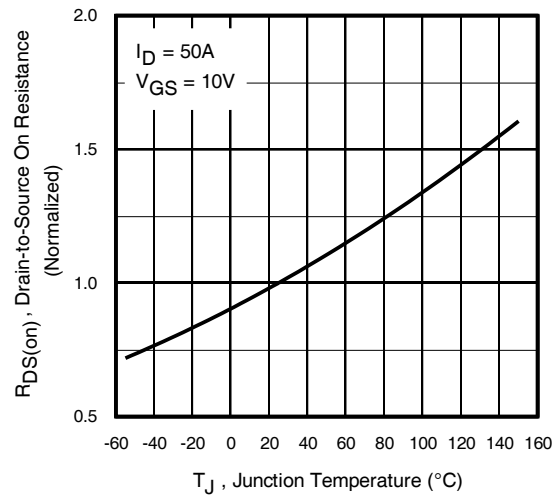
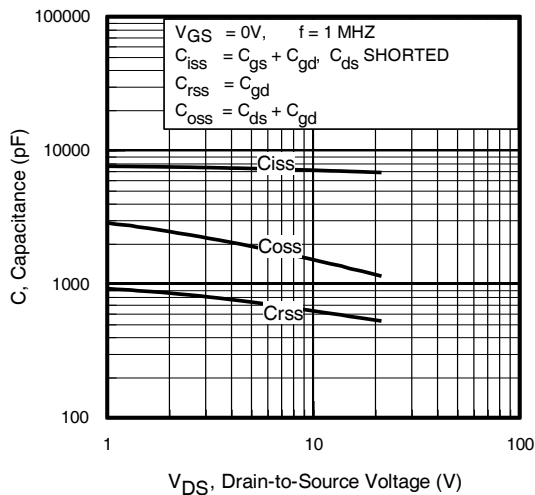
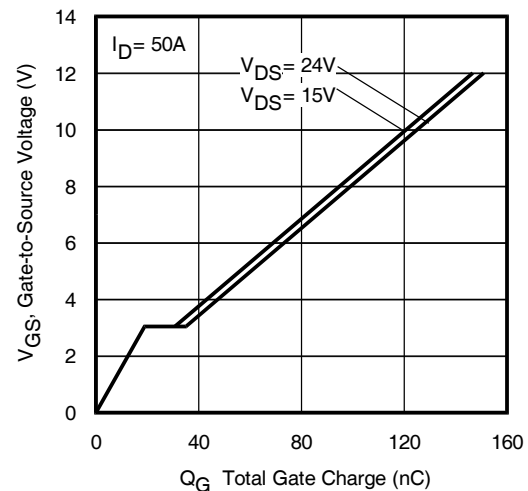
	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ②	—	420	mJ
I _{AR}	Avalanche Current ①	—	50	A

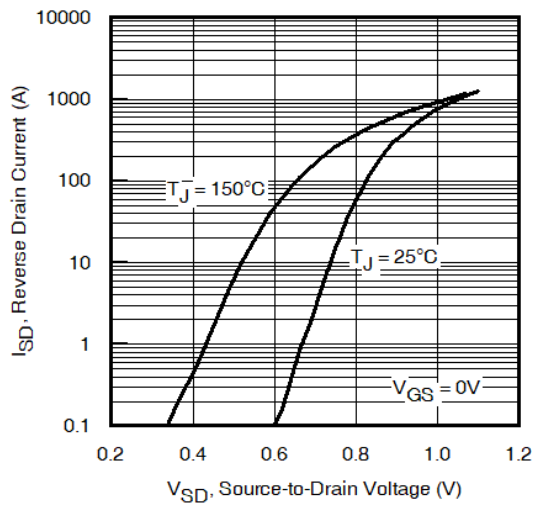
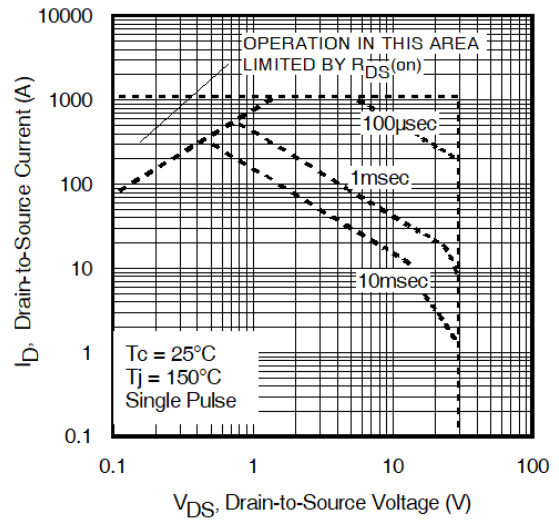
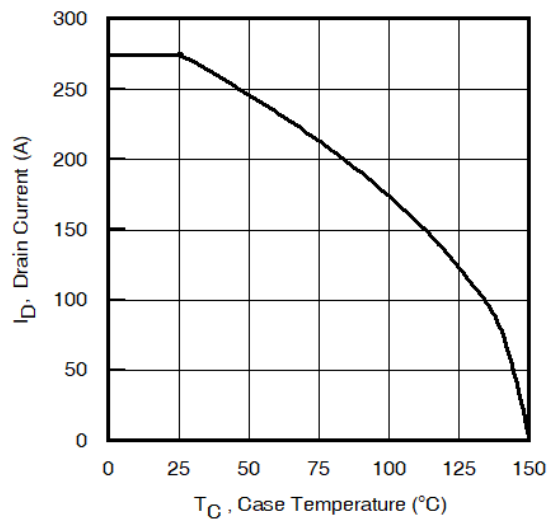
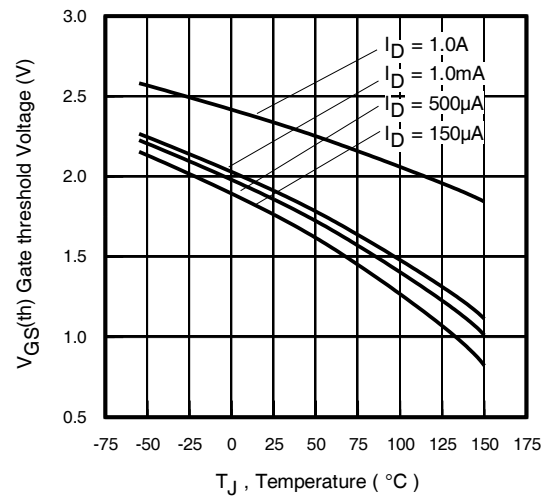
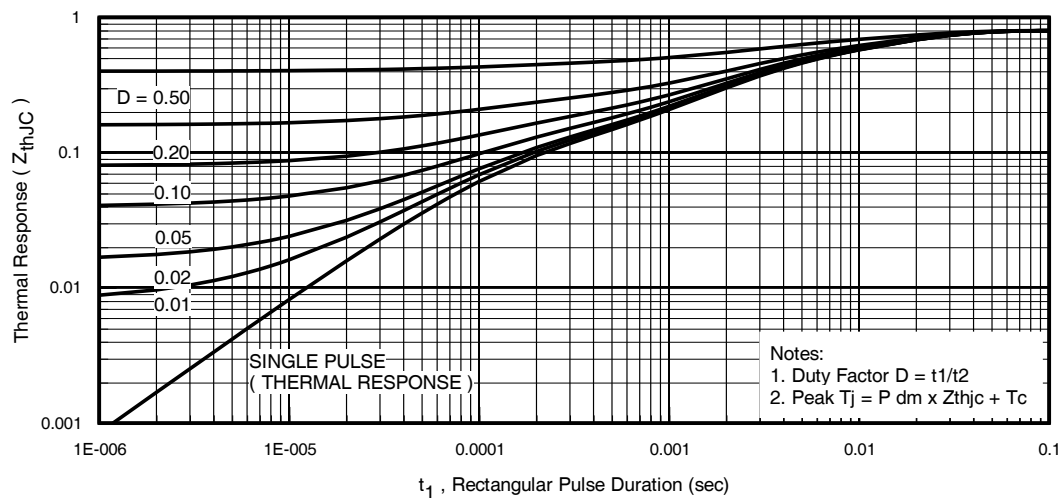
Diode Characteristics

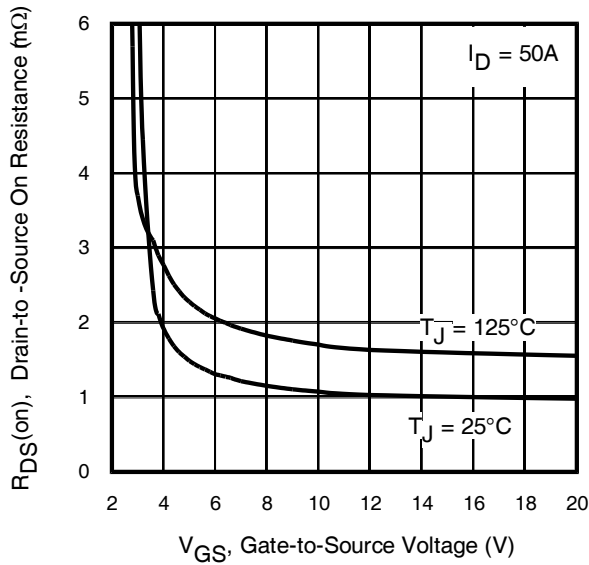
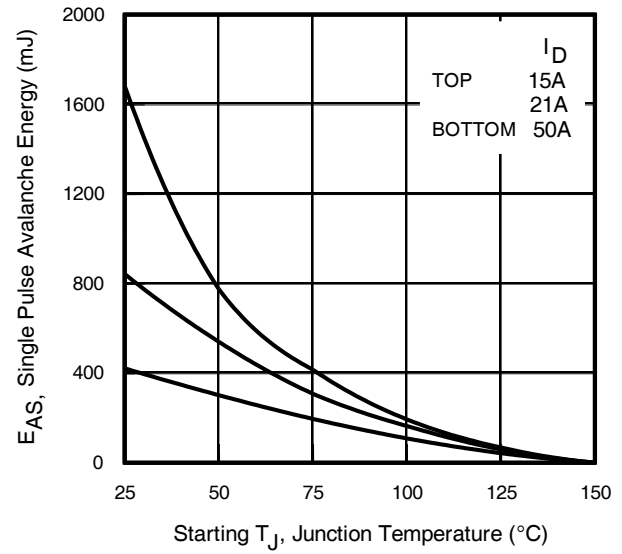
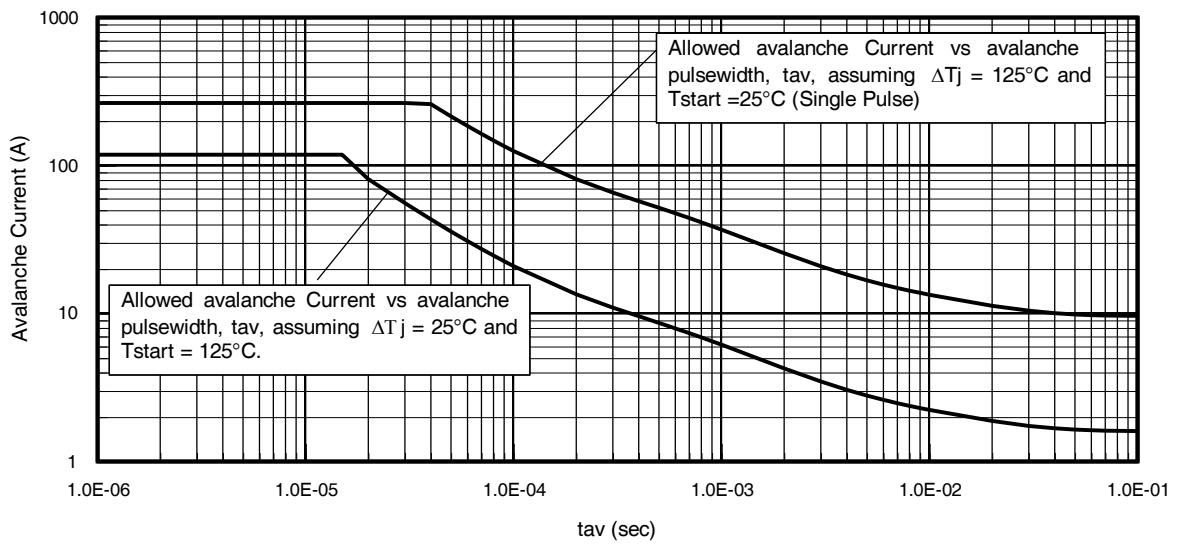
	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	156	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	1100		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 50A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	34	51	ns	T _J = 25°C, I _F = 50A, V _{DD} = 15V
Q _{rr}	Reverse Recovery Charge	—	68	100	nC	di/dt = 200A/μs ③

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC} (Bottom)	Junction-to-Case ④	0.5	0.8	°C/W
R _{θJC} (Top)	Junction-to-Case ④	—	15	
R _{θJA}	Junction-to-Ambient ⑤	—	35	
R _{θJA} (<10s)	Junction-to-Ambient ⑤	—	33	


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Threshold Voltage Vs. Temperature

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig 12. On-Resistance vs. Gate Voltage

Fig 13. Maximum Avalanche Energy vs. Drain Current

Fig 14. Typical Avalanche Current vs. Pulse width

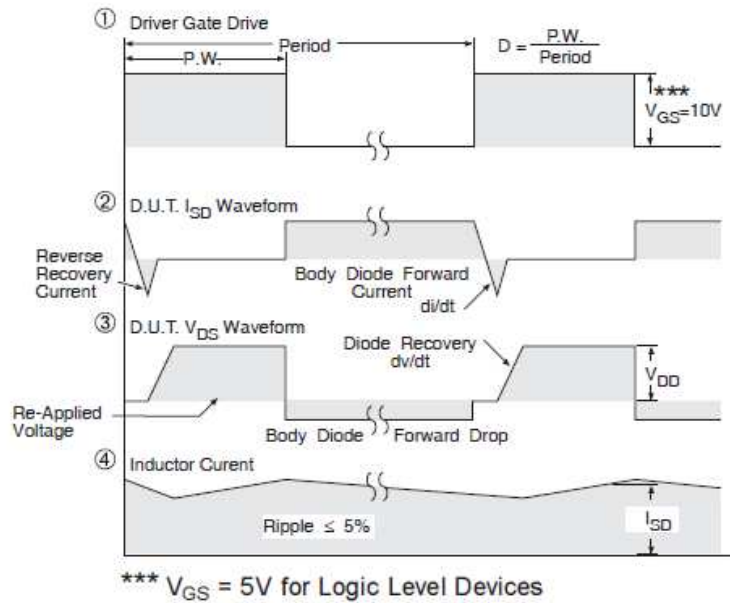
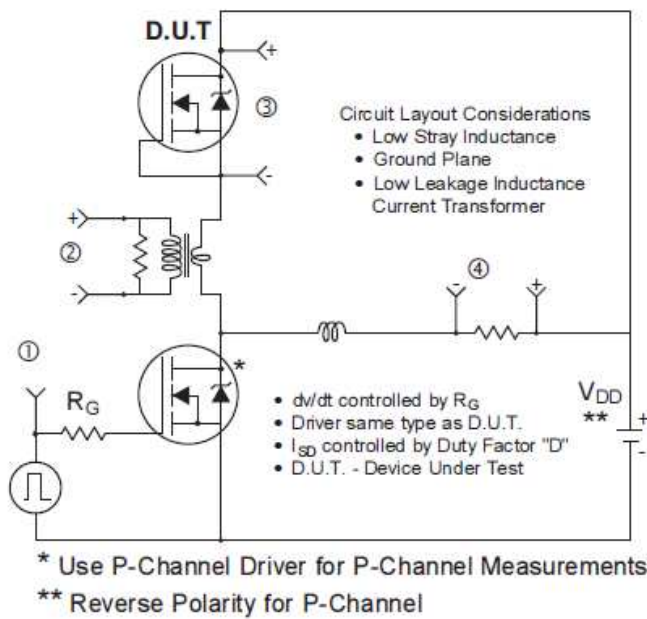


Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

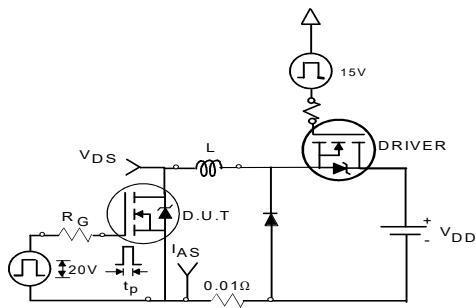


Fig 16a. Unclamped Inductive Test Circuit

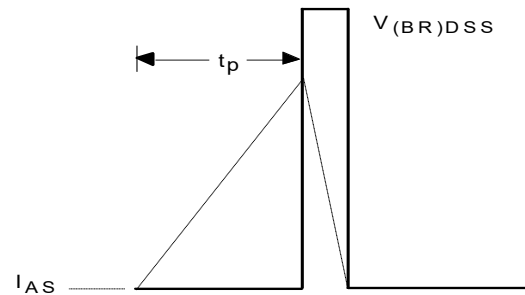


Fig 16b. Unclamped Inductive Waveforms

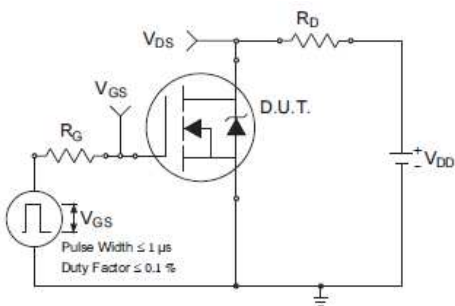


Fig 17a. Switching Time Test Circuit

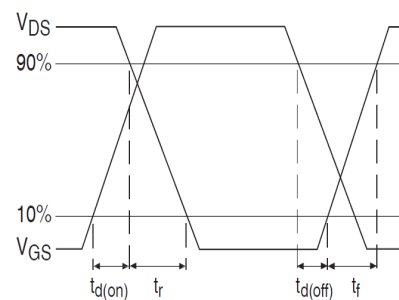


Fig 17b. Switching Time Waveforms

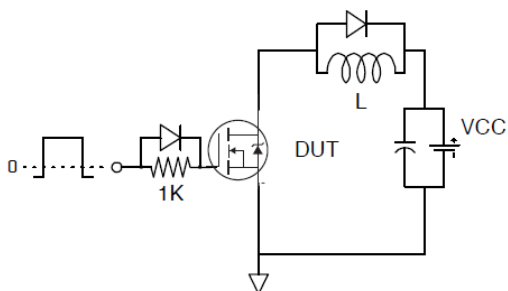


Fig 18a. Gate Charge Test Circuit

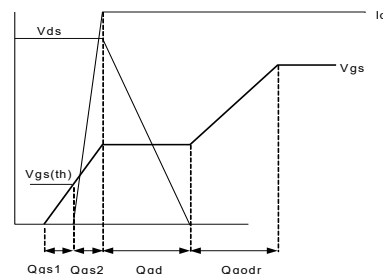
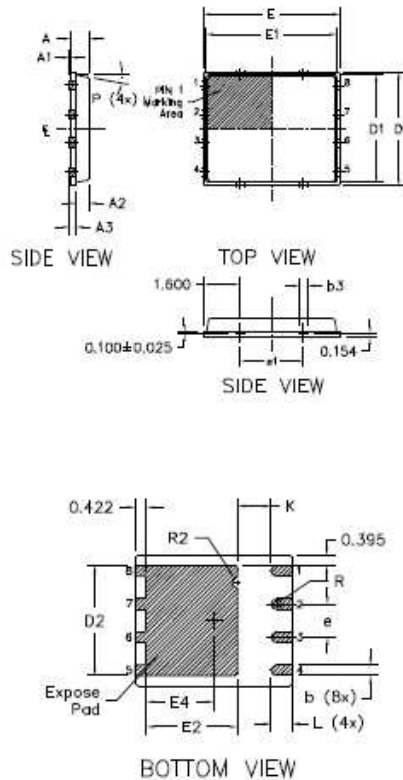


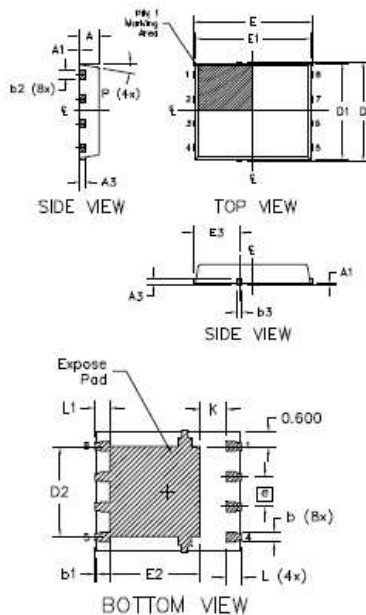
Fig 18b. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details


DIM SYMBOL	MILLIMETERS		INCH	
	MIN	MAX	MIN	MAX
A	0.800	0.900	0.0315	0.0543
A1	0.000	0.050	0.0000	0.0020
A3	0.200 REF		0.0079 REF	
b	0.350	0.470	0.0138	0.0185
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.150	0.450	0.0059	0.0177
D	5.000 BSC		0.1969 BSC	
D1	4.750 BSC		0.1870 BSC	
D2	4.100		4.300	
E	6.000 BSC		0.2362 BSC	
E1	5.750 BSC		0.2264 BSC	
E2	3.380		3.780	
e	1.270 REF		0.0500 REF	
e1	2.800 REF		0.1102 REF	
K	1.200		1.420	
L	0.710		0.900	
P	0°		12°	
R	0.200 REF		0.0079 REF	
R2	0.150		0.200	

Note:

1. Dimensions and tolerancing conform to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

PQFN 5x6 Outline "G" Package Details


DIM SYMBOL	MILLIMETERS		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.950	1.050	0.0374	0.0413
A1	0.000	0.050	0.0000	0.0020
A3	0.254 REF		0.0100 REF	
b	0.310	0.510	0.0122	0.0201
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.180	0.450	0.0071	0.0177
D	5.150 BSC		0.2028 BSC	
D1	5.000 BSC		0.1969 BSC	
D2	3.700		3.900	
E	6.150 BSC		0.2421 BSC	
E1	6.000 BSC		0.2362 BSC	
E2	3.560		3.760	
E3	2.270		2.470	
e	1.27 REF		0.050 REF	
K	0.830		1.400	
L	0.510		0.710	
L1	0.510		0.710	
P	10 deg		12 deg	

Note:

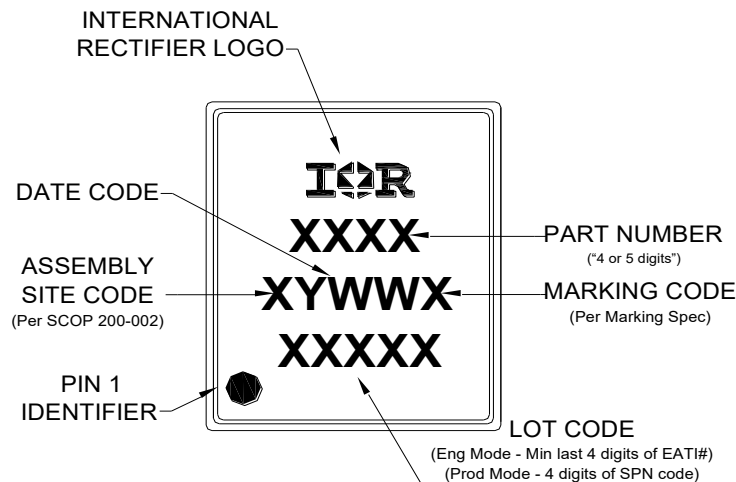
1. Dimensions and tolerancing conform to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154: <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

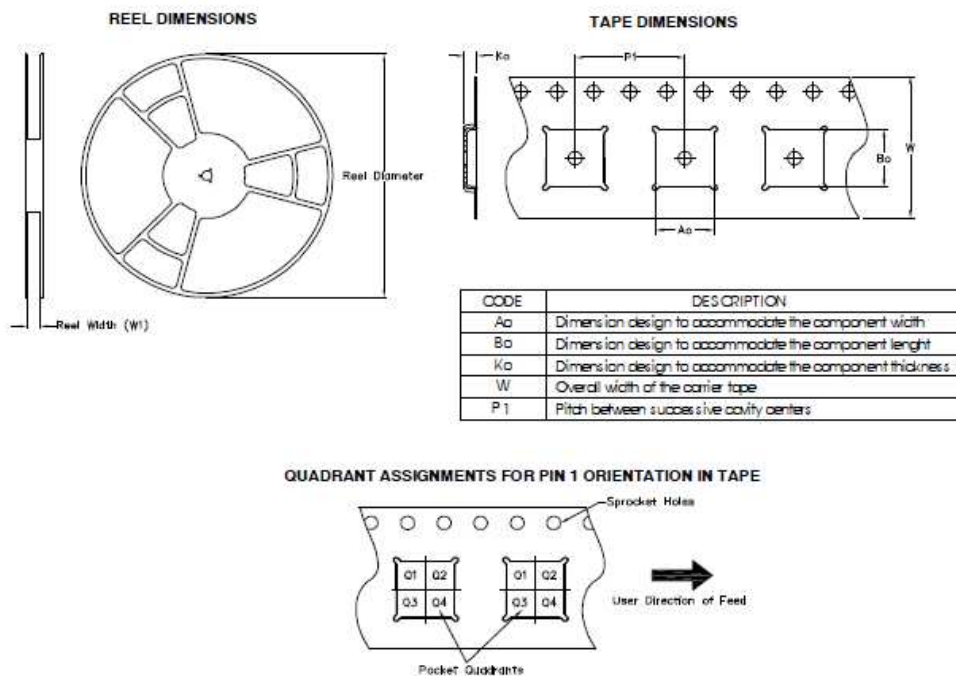
Note: For the most current drawing please refer to website at <http://www.irf.com/packaging>

PQFN 5x6 Part Marking



Note: For the most current drawing please refer to website at <http://www.irf.com/packaging>

PQFN 5x6 Tape and Reel



Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ka (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
5 X 6 PQFN	13	4000	12.4	6.300	5.300	1.20	8.00	12	Q1

Note: For the most current drawing please refer to website at <http://www.irf.com/packaging>

Qualification Information

Qualification Level	Industrial (per JEDEC JESD47F [†] guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D [†])
RoHS Compliant	Yes	

[†] Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}\text{C}$, $L = 0.337\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 50\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_{θ} is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square PCB (FR-4). Please refer to AN-994 for more details:
<http://www.irf.com/technical-info/appnotes/an-994.pdf>
- ⑥ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C . For higher case temperature please refer to Diagram 9. De-rating will be required based on the actual environmental conditions.

Revision History

Date	Rev.	Comments
03/28/2012	2.1	Updated package outline on page 7.
08/01/2013	2.2	Added "StrongIRFET™" above part number on page 1
04/28/2015	2.3	- Updated package outline for "option B" and added package outline for "option G" on page 7. - Updated tape and reel on page 8.
05/19/2015	2.4	- Updated package outline for "option G" on page 7. - Updated "IFX logo" on page 1 and page 9.
02/27/2020	2.5	- Changed datasheet with Infineon logo - all pages - Added disclaimer on last page - Removed "HEXFET™ POWER MOSFET" -page 1
03/17/2021	2.6	- Updated datasheet based on IFX template. - Updated Datasheet based on new current rating and application note : App-AN_1912_PL51_2001_180356

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